1. General description

PNP/PNP general-purpose transistor in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: BC847QAS.

NPN/PNP complement: BC847QAPN.

2. Features and benefits

- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified
- Low package height of 0.37 mm

3. Applications

- General-purpose switching and amplification
- Mobile applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
V _{CEO}	collector-emitter voltage	open base		-	-	-45	V
I _C	collector current			-	-	-100	mA
Per transistor							
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C		200	-	450	





45 V, 100 mA PNP/PNP general-purpose transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		6 5 4
2	B1	base TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix} \begin{bmatrix} 6 \\ 6 \end{bmatrix}$	P = 200
3	C2	collector TR2	2 5	(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2	3 4	1 2 3
6	C1	collector TR1	Transparent top view	sym018
7	C1	collector TR1	DFN1010B-6 (SOT1216)	
8	C2	collector TR2		

6. Ordering information

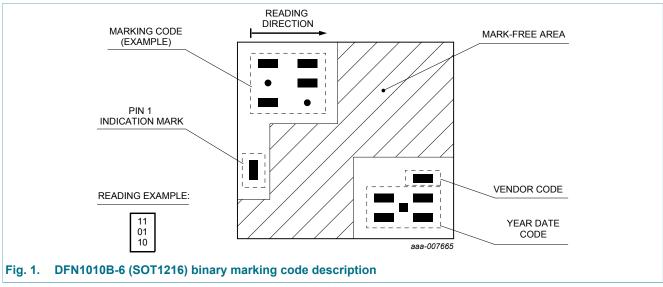
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BC857QAS	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216		

7. Marking

Table 4. Marking codes

Type number	Marking code
BC857QAS	10 01 00



BC857QAS

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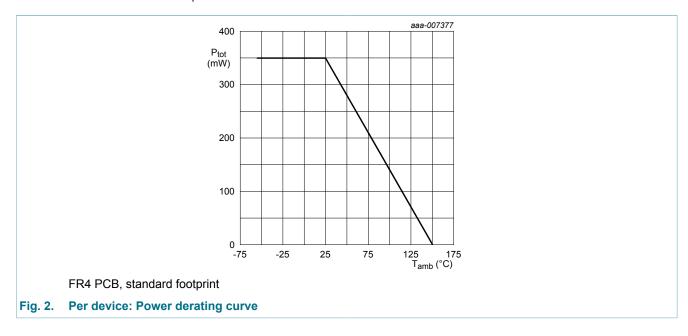
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor	'				
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-45	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-200	mA
I _{BM}	peak base current			-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	230	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	350	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

 Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	r						
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	543	K/W
Per device							
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

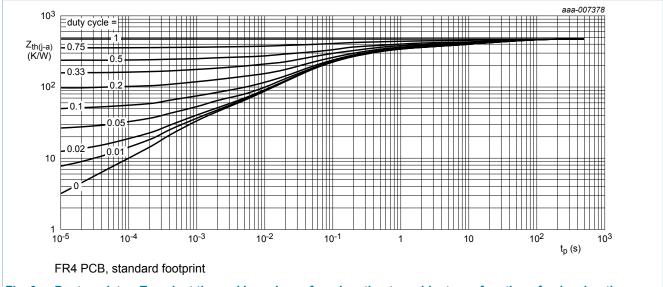


Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

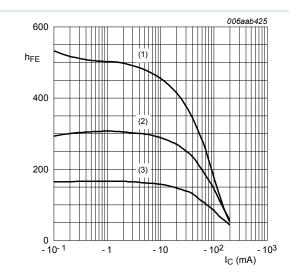
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
I _{CBO}	collector-base cut-off	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-5	μA
	current	V_{CB} = -30 V; I_E = 0 A; T_{amb} = 25 °C	-	-	-15	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C	200	-	450	
V _{CEsat}	collector-emitter	I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C	-	-	-100	mV
	saturation voltage	I_{C} = -100 mA; I_{B} = -5 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	-300	mV
V _{BEsat}	base-emitter saturation voltage	I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C	-	-760	-	mV
V _{BEsat}	base-emitter saturation voltage	I_{C} = -100 mA; I_{B} = -5 mA; pulsed; t_{p} ≤ 300 μ s; δ ≤ 0.02; T_{amb} = 25 °C	-	-900	-	mV
V_{BE}	base-emitter voltage	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C	-600	-660	-725	mV
V_{BE}	base-emitter voltage	V_{CE} = -5 V; I_{C} = -10 mA; T_{amb} = 25 °C	-	-710	-820	mV
C _C	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	4	pF
C _E	emitter capacitance	V_{EB} = -0.5 V; I_{C} = 0 A; f = 1 MHz; T_{amb} = 25 ##C	-	10	-	pF
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
NF	noise figure	V_{CE} = -5 V; I_{C} = 0.2 mA; R_{S} = 2 k Ω ; f = 1 MHz; B = 200 Hz; T_{amb} = 25 °C	-	-	10	dB

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$$V_{CE} = -5 V$$

(1)
$$T_{amb}$$
 = 150 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 4. DC current gain as a function of collector current; typical values

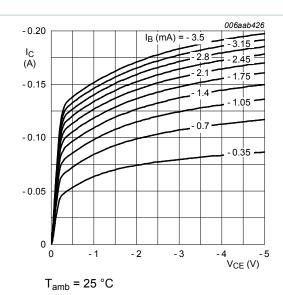
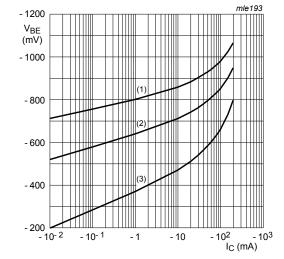


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



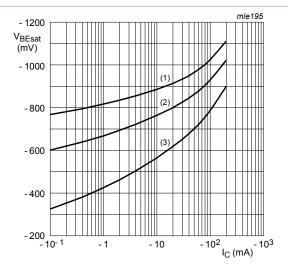
$$V_{CE} = -5 V$$

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 150 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

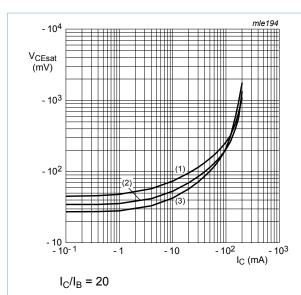
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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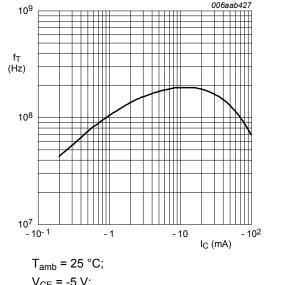


(1)
$$T_{amb}$$
 = 150 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



 $V_{CE} = -5 V;$

f = 100 MHz

Fig. 9. Transition frequency as a function of collector current; typical values

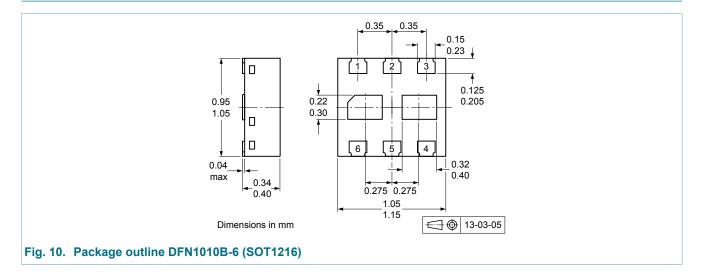
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11. Test information

11.1 Quality information

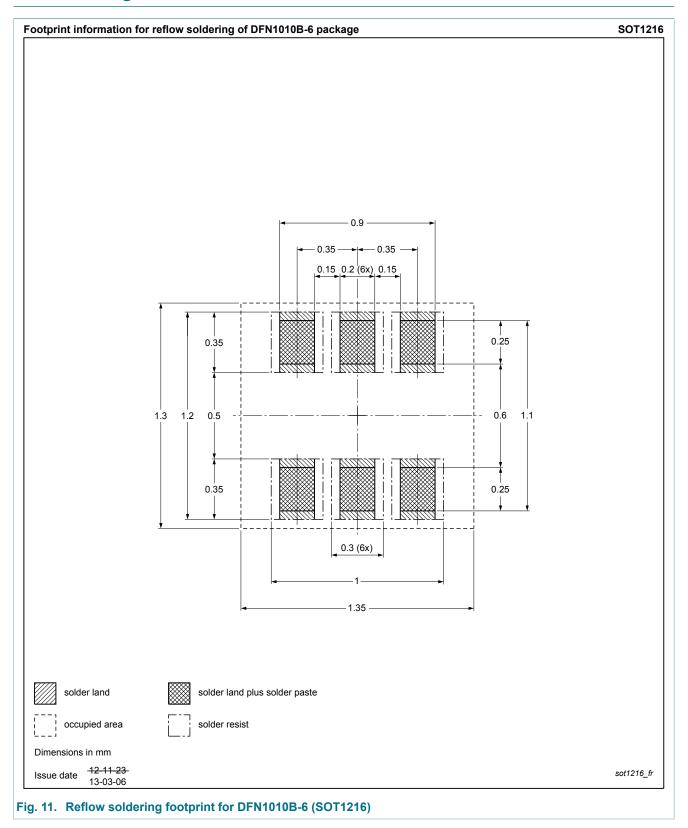
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



BC857QAS

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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC857QAS v.1	20140725	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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